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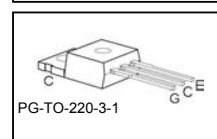
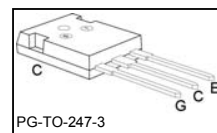
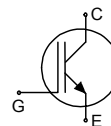
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SGP10N60A SGW10N60A

Fast IGBT in NPT-technology

- 75% lower E_{off} compared to previous generation combined with low conduction losses
- Short circuit withstand time – 10 μ s
- Designed for:
 - Motor controls
 - Inverter
- NPT-Technology for 600V applications offers:
 - very tight parameter distribution
 - high ruggedness, temperature stable behaviour
 - parallel switching capability
- Qualified according to JEDEC¹ for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	V_{CE}	I_C	$V_{CE(sat)}$	T_j	Marking	Package
SGP10N60A	600V	10A	2.3V	150°C	G10N60A	PG-TO-220-3-1
SGW10N60A	600V	10A	2.3V	150°C	G10N60A	PG-TO-247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current	I_C	20	A
$T_C = 25^\circ\text{C}$		10.6	
$T_C = 100^\circ\text{C}$			
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	40	
Turn off safe operating area	-	40	
$V_{CE} \leq 600\text{V}$, $T_j \leq 150^\circ\text{C}$			
Gate-emitter voltage	V_{GE}	± 20	V
Avalanche energy, single pulse	E_{AS}	70	mJ
$I_C = 10\text{ A}$, $V_{CC} = 50\text{ V}$, $R_{GE} = 25\ \Omega$, start at $T_j = 25^\circ\text{C}$			
Short circuit withstand time ²	t_{SC}	10	μ s
$V_{GE} = 15\text{V}$, $V_{CC} \leq 600\text{V}$, $T_j \leq 150^\circ\text{C}$			
Power dissipation	P_{tot}	92	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wavesoldering, 1.6mm (0.063 in.) from case for 10s	T_s	260	

¹ J-STD-020 and JESD-022

² Allowed number of short circuits: <1000; time between short circuits: >1s.



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Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		1.35	K/W
Thermal resistance, junction – ambient	R_{thJA}	PG-TO-220-3-1 PG-TO-247-3-21	62 40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=10A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	1.7 -	2 2.3	2.4 2.8	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=300\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	- -	40 1500	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=10A$	-	6.7	-	S
Dynamic Characteristic						
Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$	-	550	660	pF
Output capacitance	C_{oss}		-	62	75	
Reverse transfer capacitance	C_{rss}		-	42	51	
Gate charge	Q_{Gate}	$V_{CC}=480V, I_C=10A$ $V_{GE}=15V$	-	52	68	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E	PG-TO-220-3-1 PG-TO-247-3-21	- -	7 13	- -	nH
Short circuit collector current ²⁾	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $V_{CC}\leq 600V,$ $T_j\leq 150^\circ\text{C}$	-	100	-	A

²⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.



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Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=10\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=25\Omega$, $L_\sigma^{(1)}=180\text{nH}$, $C_\sigma^{(1)}=55\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	28	34	ns
Rise time	t_r		-	12	15	
Turn-off delay time	$t_{d(off)}$		-	178	214	
Fall time	t_f		-	24	29	
Turn-on energy	E_{on}		-	0.15	0.173	mJ
Turn-off energy	E_{off}		-	0.17	0.221	
Total switching energy	E_{ts}		-	0.320	0.394	

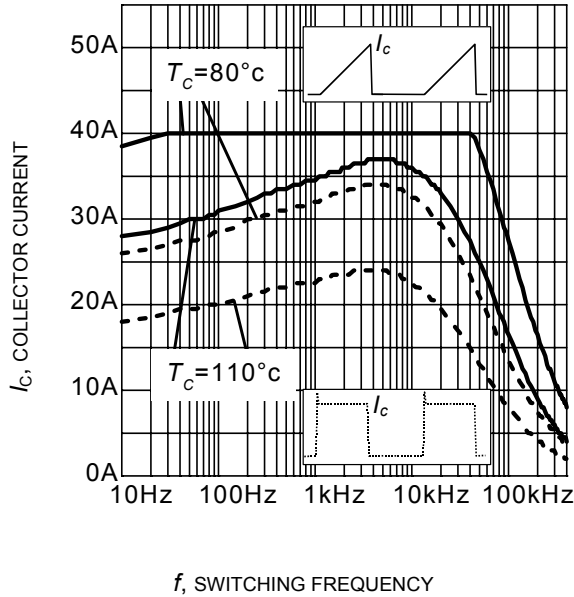
Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$, $I_C=10\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=25\Omega$, $L_\sigma^{(1)}=180\text{nH}$, $C_\sigma^{(1)}=55\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	28	34	ns
Rise time	t_r		-	12	15	
Turn-off delay time	$t_{d(off)}$		-	198	238	
Fall time	t_f		-	26	32	
Turn-on energy	E_{on}		-	0.260	0.299	mJ
Turn-off energy	E_{off}		-	0.280	0.364	
Total switching energy	E_{ts}		-	0.540	0.663	

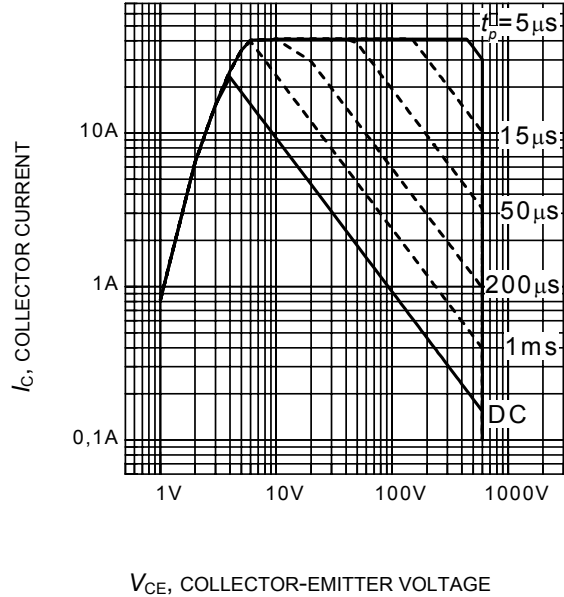
¹⁾ Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit in Figure E.



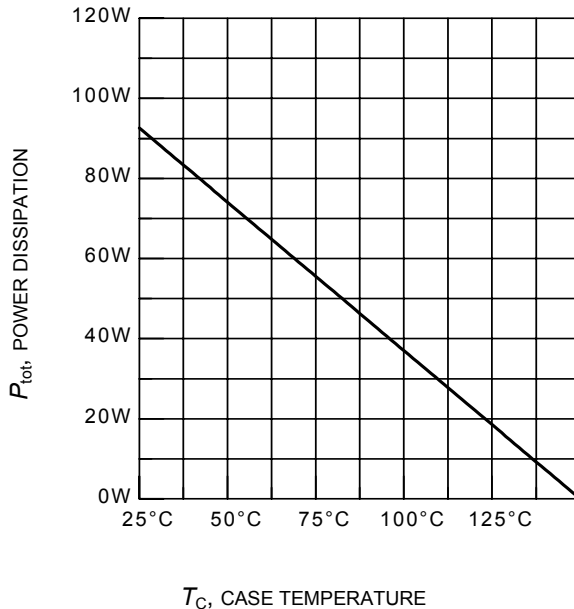
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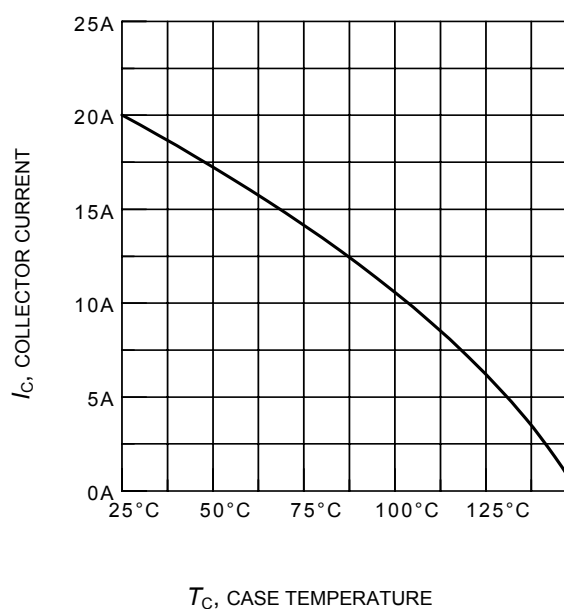
f , SWITCHING FREQUENCY
Figure 1. Collector current as a function of switching frequency
 $(T_J \leq 150^\circ\text{C}, D = 0.5, V_{CE} = 400\text{V}, V_{GE} = 0/+15\text{V}, R_G = 25\Omega)$



V_{CE} , COLLECTOR-EMITTER VOLTAGE
Figure 2. Safe operating area
 $(D = 0, T_C = 25^\circ\text{C}, T_J \leq 150^\circ\text{C})$



T_C , CASE TEMPERATURE
Figure 3. Power dissipation as a function of case temperature
 $(T_J \leq 150^\circ\text{C})$



T_C , CASE TEMPERATURE
Figure 4. Collector current as a function of case temperature
 $(V_{GE} \leq 15\text{V}, T_J \leq 150^\circ\text{C})$



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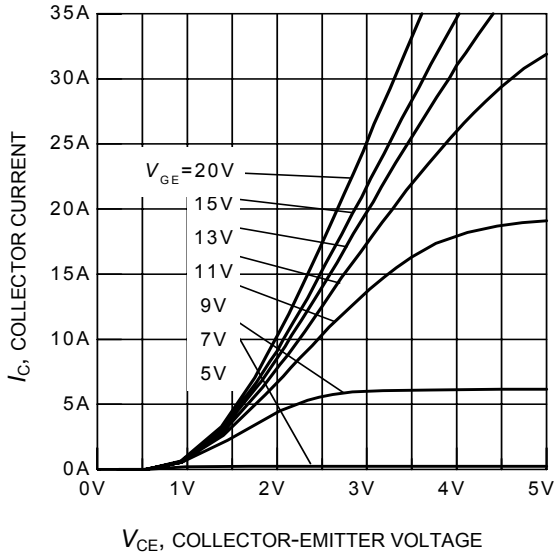


Figure 5. Typical output characteristics
($T_j = 25^\circ\text{C}$)

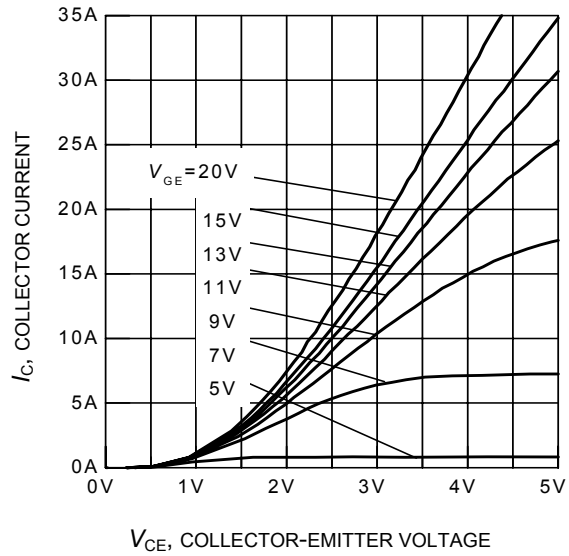


Figure 6. Typical output characteristics
($T_j = 150^\circ\text{C}$)

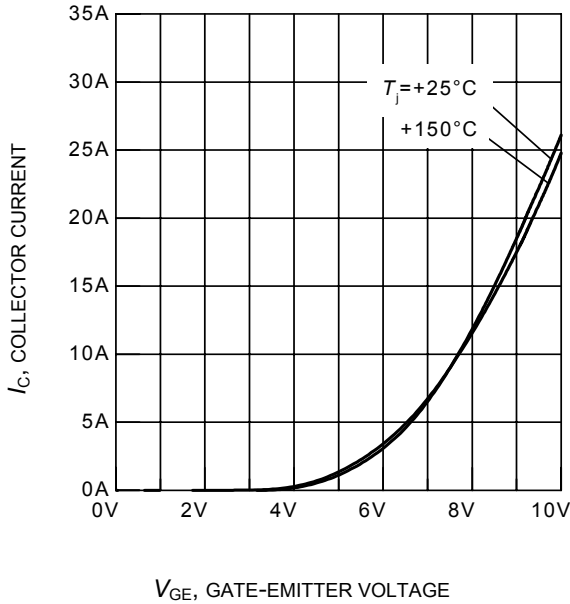


Figure 7. Typical transfer characteristics
($V_{CE} = 10\text{V}$)

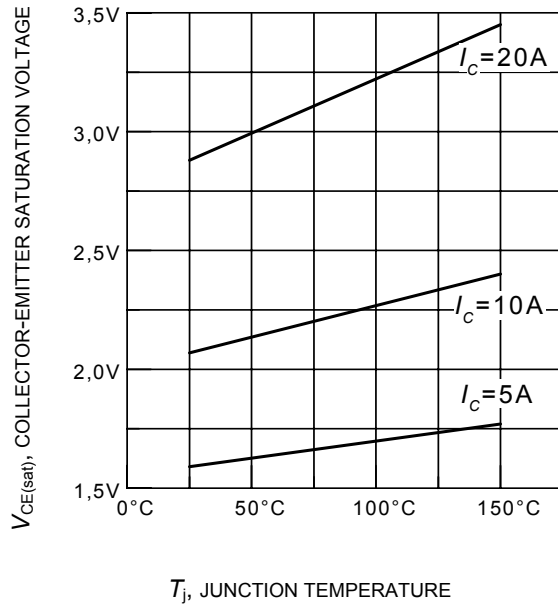
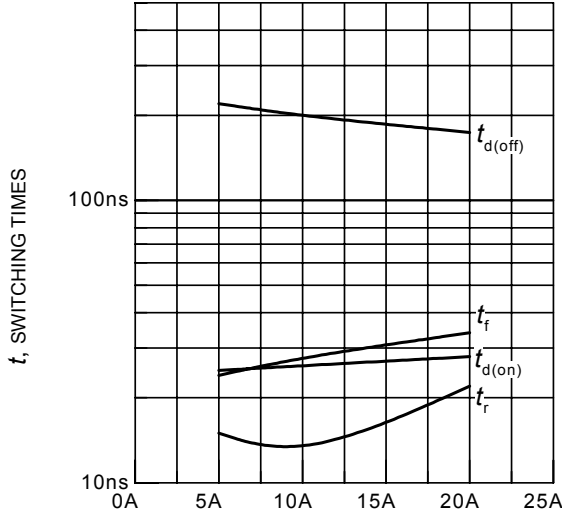


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

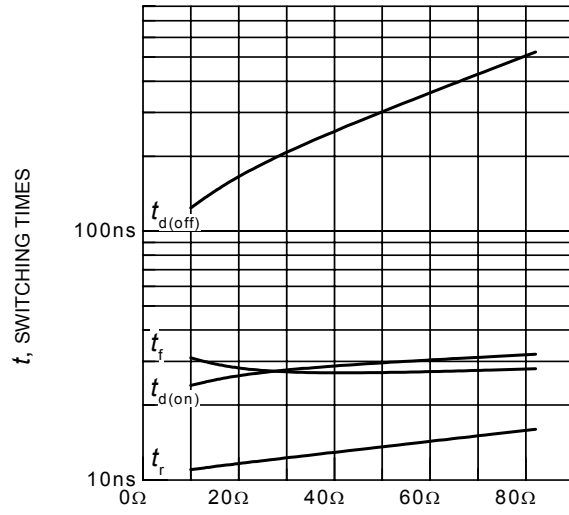


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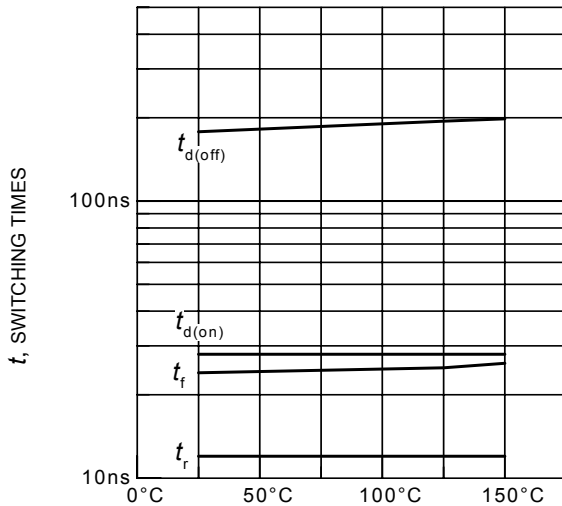
I_C , COLLECTOR CURRENT

Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 25\Omega$,
 Dynamic test circuit in Figure E)



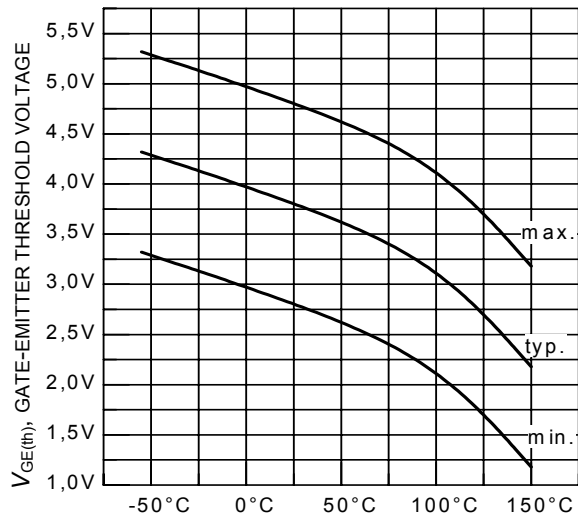
R_G , GATE RESISTOR

Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 10\text{A}$,
 Dynamic test circuit in Figure E)



T_j , JUNCTION TEMPERATURE

Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$,
 $I_C = 10\text{A}$, $R_G = 25\Omega$,
 Dynamic test circuit in Figure E)

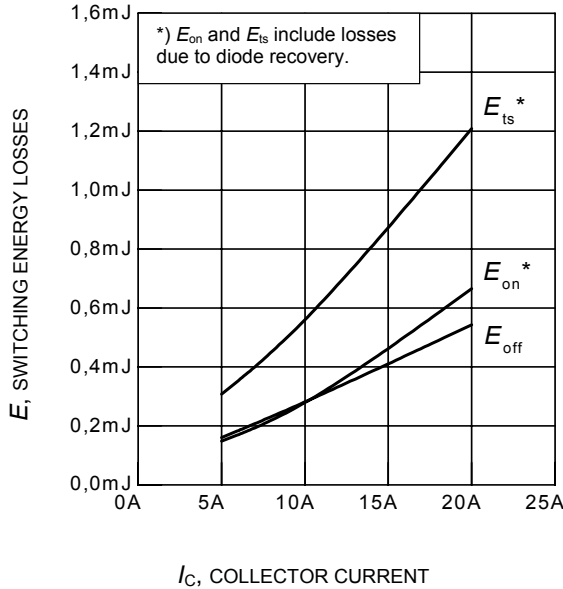


T_j , JUNCTION TEMPERATURE

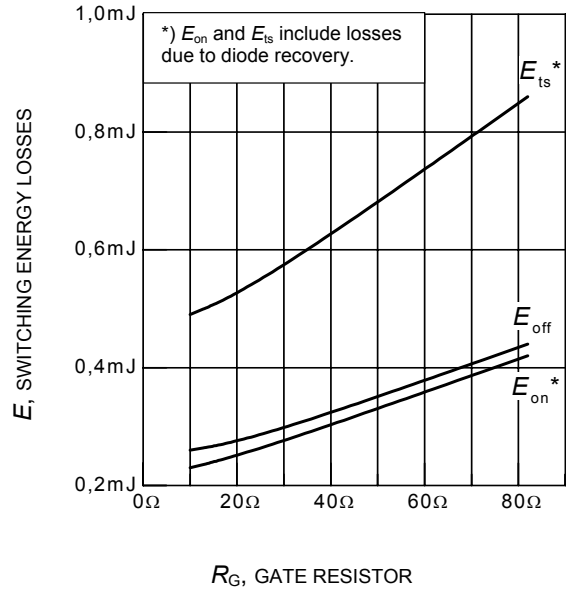
Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C = 0.3\text{mA}$)



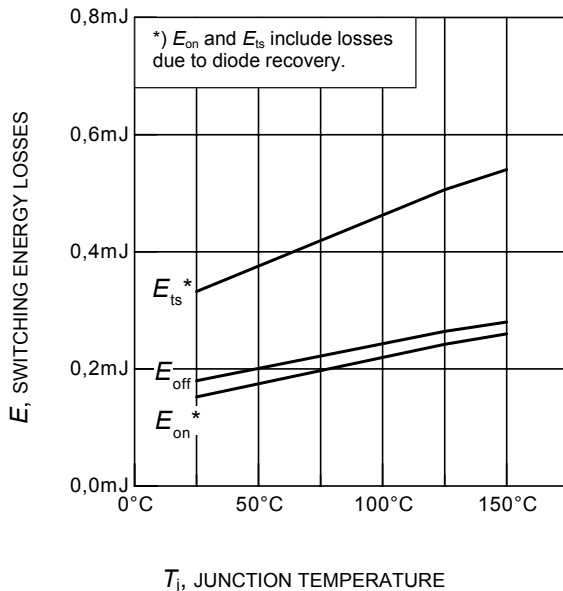
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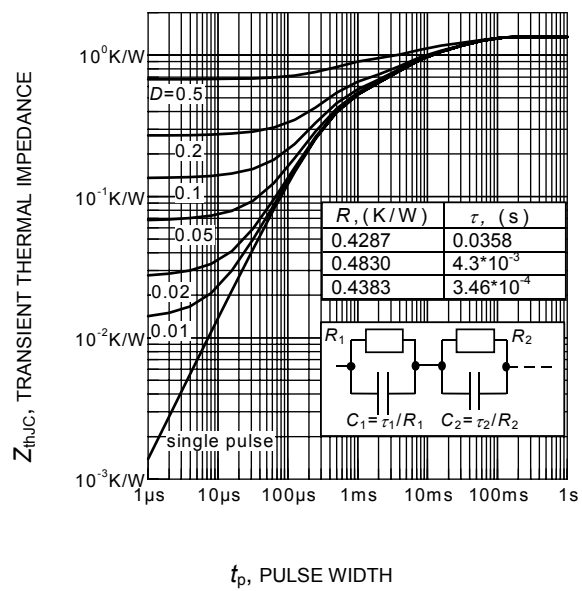
I_C , COLLECTOR CURRENT
Figure 13. Typical switching energy losses as a function of collector current
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 25\Omega$, Dynamic test circuit in Figure E)



R_G , GATE RESISTOR
Figure 14. Typical switching energy losses as a function of gate resistor
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 10\text{A}$, Dynamic test circuit in Figure E)



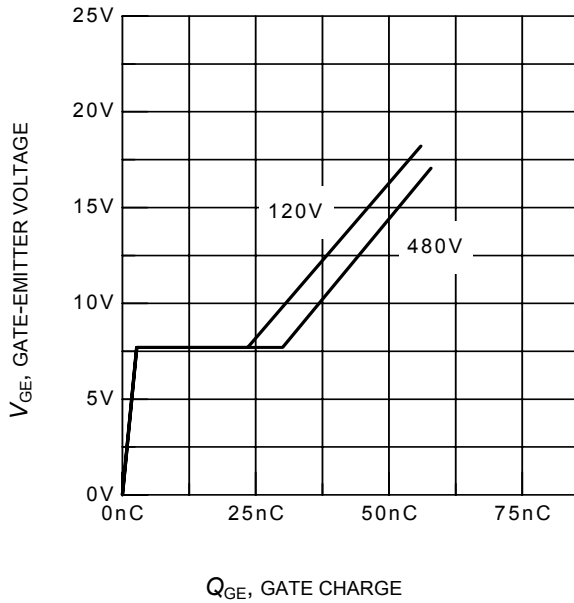
T_j , JUNCTION TEMPERATURE
Figure 15. Typical switching energy losses as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 10\text{A}$, $R_G = 25\Omega$, Dynamic test circuit in Figure E)



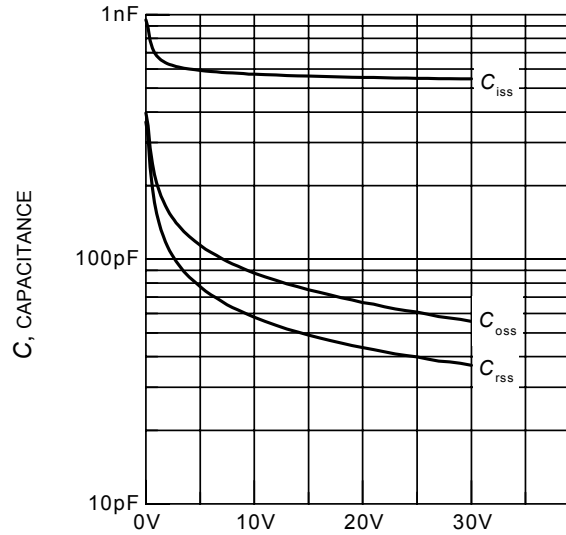
t_p , PULSE WIDTH
Figure 16. IGBT transient thermal impedance as a function of pulse width
 ($D = t_p / T$)



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Q_{GE} , GATE CHARGE
Figure 17. Typical gate charge
 ($I_C = 10A$)



V_{CE} , COLLECTOR-EMITTER VOLTAGE
Figure 18. Typical capacitance as a function of collector-emitter voltage
 ($V_{GE} = 0V, f = 1MHz$)

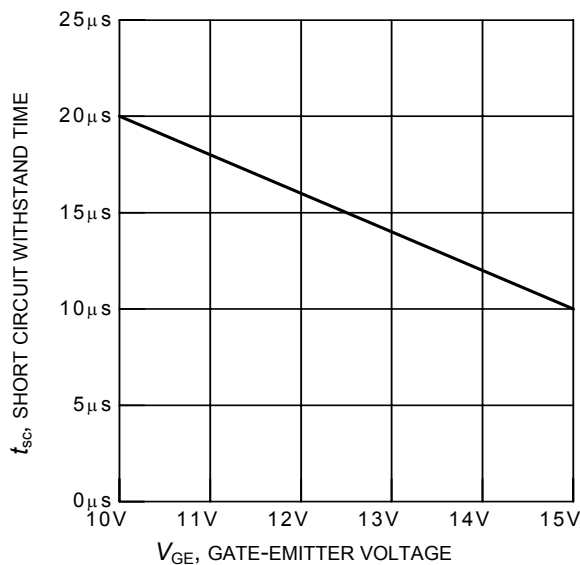


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
 ($V_{CE} = 600V$, start at $T_j = 25^\circ C$)

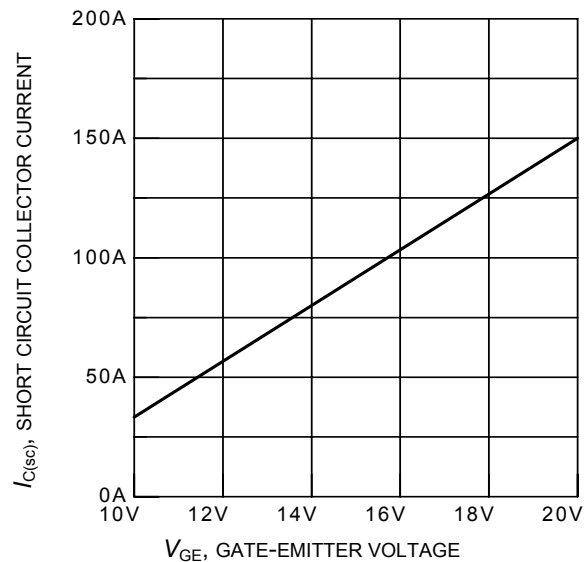
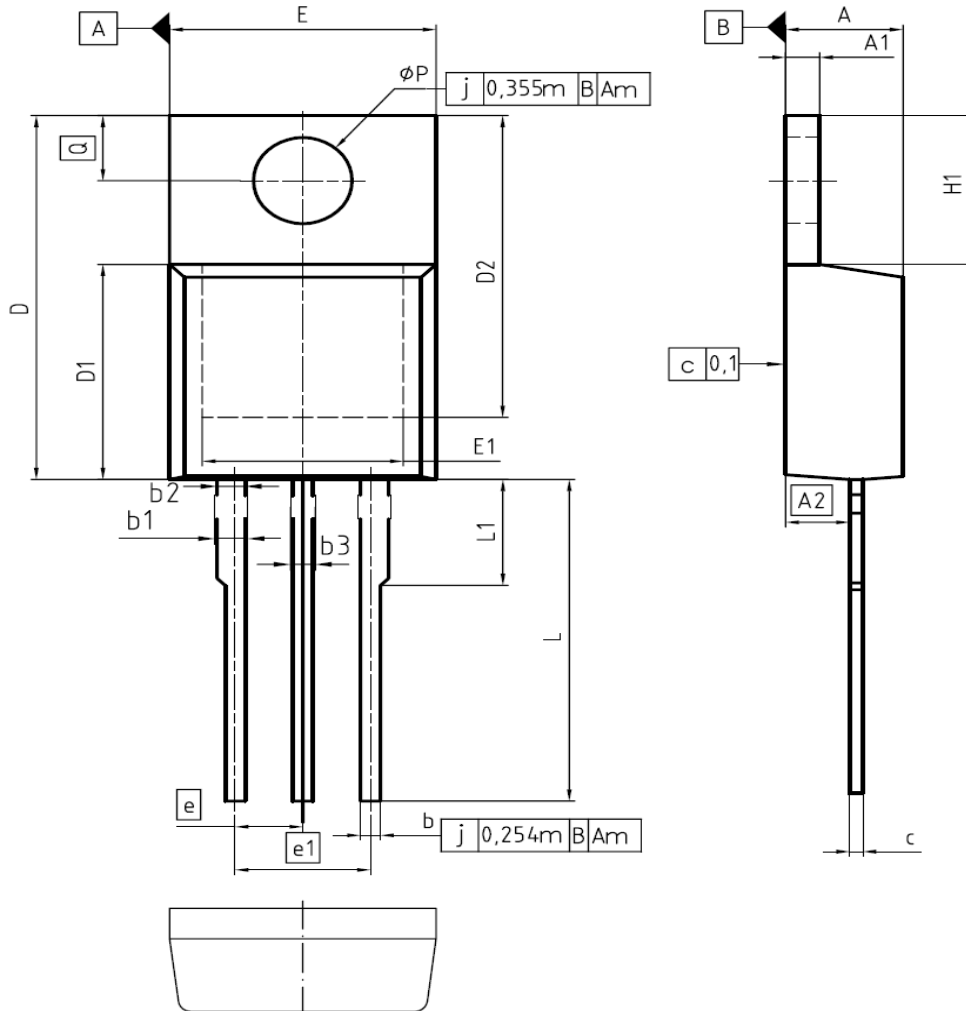


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
 ($V_{CE} \leq 600V, T_j = 150^\circ C$)



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PG-TO220-3-1



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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SCALE

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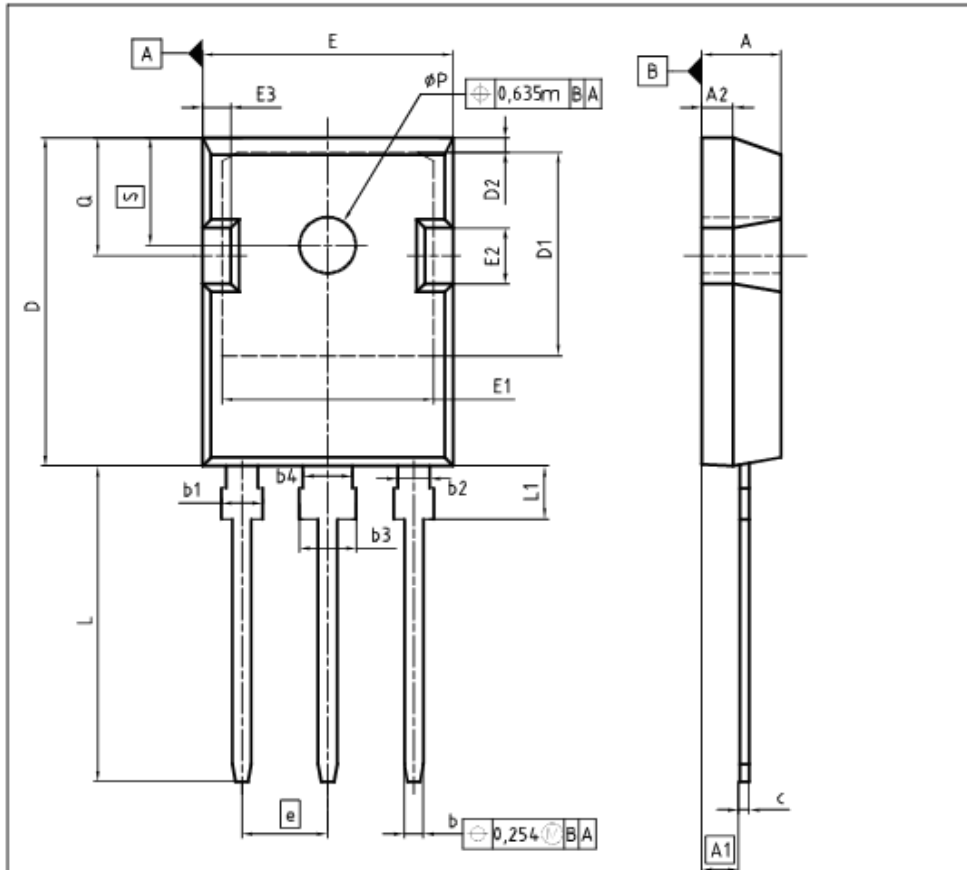
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05



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TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.63	5.21	0.180	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	18.25	17.85	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
eP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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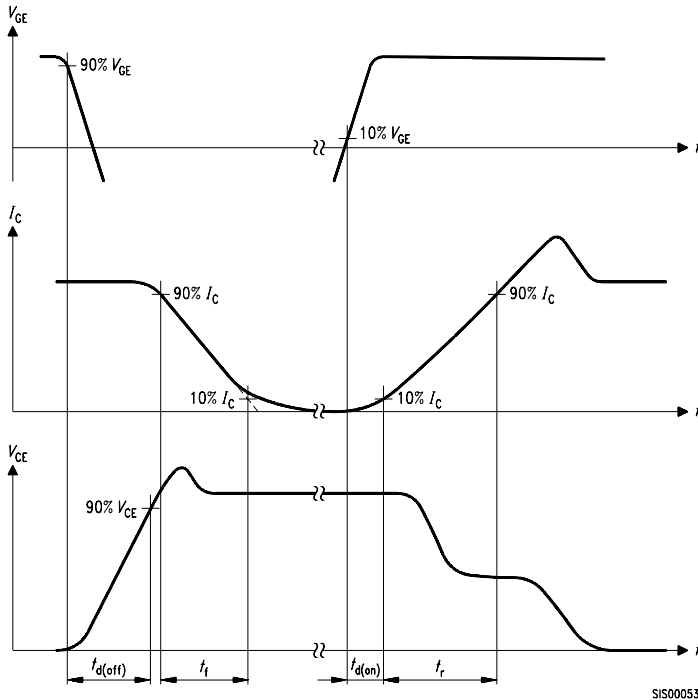


Figure A. Definition of switching times

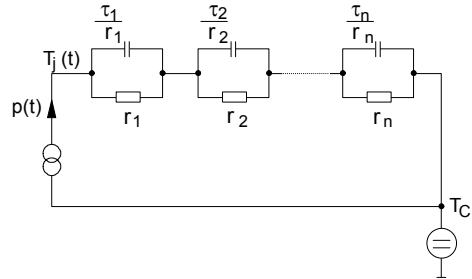


Figure D. Thermal equivalent circuit

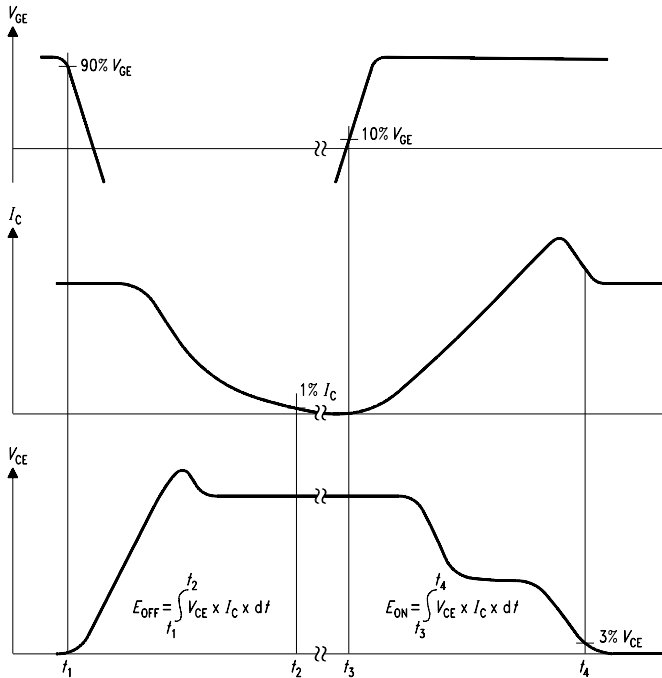


Figure B. Definition of switching losses

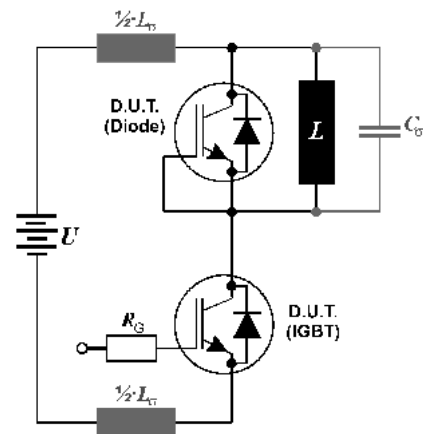


Figure E. Dynamic test circuit
 Leakage inductance $L_{\sigma} = 180\text{nH}$
 and Stray capacity $C_{\sigma} = 55\text{pF}$.



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